

/ Descriptions

WR06S ММ SQS æ M ç s ll 1 Silicon PNP transistor in a TO-3P Plastic Package.

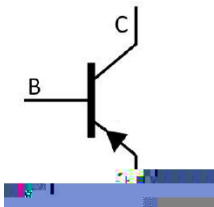
/ Features

Н, ¢ ß ll l ß ll u ` V K l Ъ WLS68F Ы
Low leakage current, high current gain bandwidth product, Complementary to TIP35C.

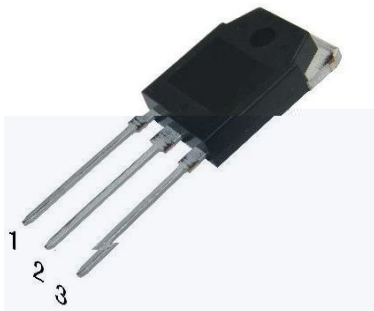
/ Applications

Ѓ ¢ l ' Õ æ H ð Æ H Z ı
Amplifier and switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

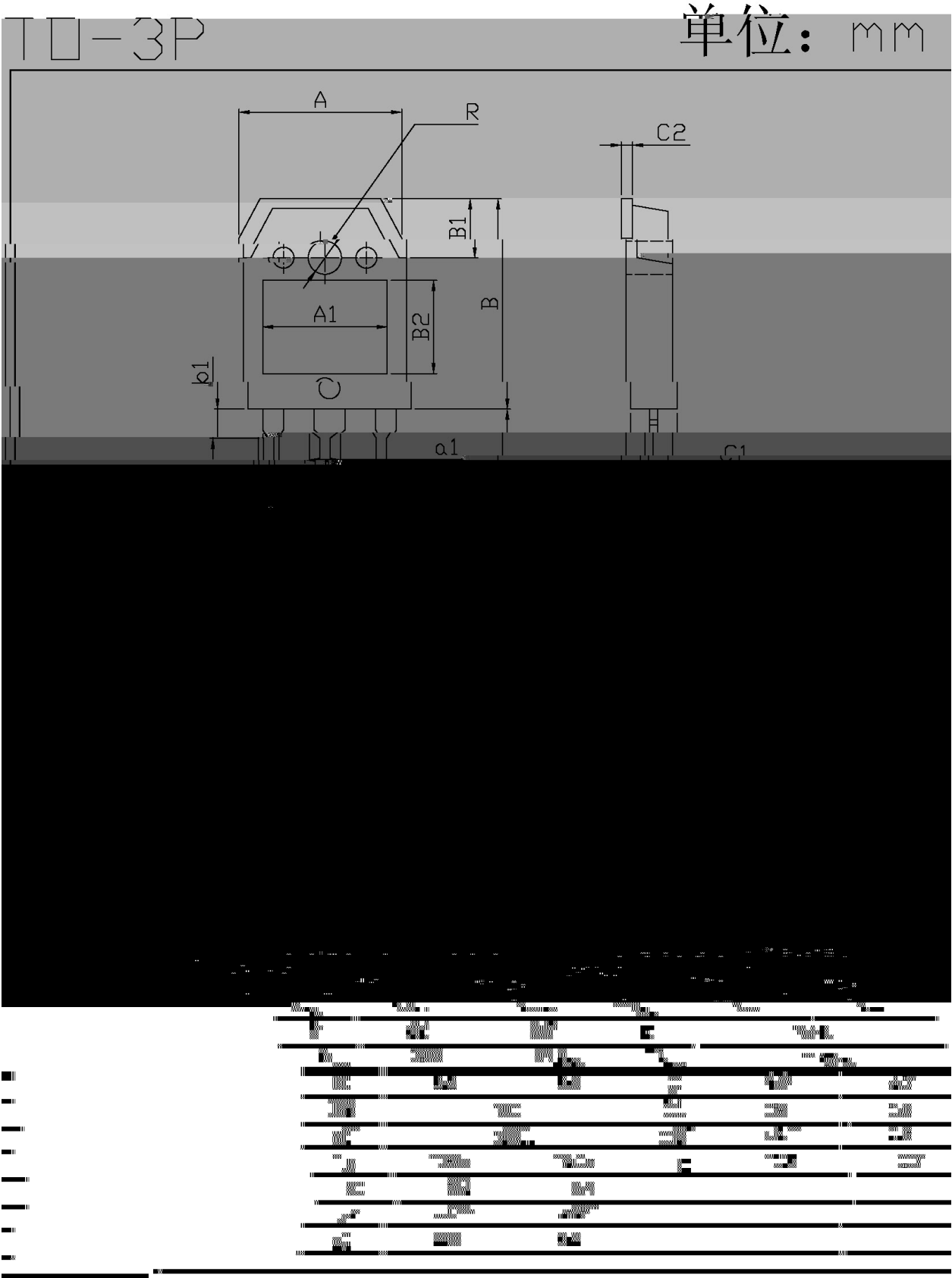
М ı " See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-25	A
Peak Collector Current	I_{CM}	-50	A
Base Current	I_B	-5	A
Total Power Dissipation	P_{tot}	125	W
Junction Temperature	T_J	175	°C
Storage Temperature Range	T_{stg}	-65 ~ 150	
Thermal Resistance Junction	R_{thj}	1	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60V$ $I_B=0$			-1	mA
Collector Cut-Off Current	I_{CES}	$V_{CE}=-60V$ $V_{BE}=0$			23a	

Figure 1 consists of three graphs showing the power dissipation capability of the 2N2639 PNP transistor. The top graph shows the relationship between collector current (I_C) and collector-emitter voltage (V_{CE}) for a pulse width of 100 μs at $T_C = 25^\circ C$. The middle graph shows the relationship for a pulse width of 1.0 ms at $T_C = 25^\circ C$. The bottom graph shows the relationship for a pulse width of 1.0 ms at $T_C = 100^\circ C$. The graphs indicate the thermal limit, secondary breakdown, and bonding wire limit.

/ Package Dimensions



Lot No. Code, code change with Lot No.

TIP36C
Rev.E Mar.-2016